506863376 09/10/2021

# PATENT ASSIGNMENT COVER SHEET

Electronic Version v1.1 Stylesheet Version v1.2 EPAS ID: PAT6910196

SUBMISSION TYPE:	NEW ASSIGNMENT
NATURE OF CONVEYANCE:	ASSIGNMENT
SEQUENCE:	3

## **CONVEYING PARTY DATA**

Name	Execution Date
SUNEDISON SEMICONDUCTOR LIMITED (UEN201334164H)	06/06/2018

## **RECEIVING PARTY DATA**

Name:	GLOBALWAFERS CO., LTD.
Street Address:	NO. 8. INDUSTRIAL EAST ROAD
Internal Address:	SCIENCE-BASED INDUSTRIAL PARK
City:	HSINCHU
State/Country:	TAIWAN

## **PROPERTY NUMBERS Total: 1**

Property Type	Number
Application Number:	17471641

### CORRESPONDENCE DATA

Fax Number: (314)612-2307

Correspondence will be sent to the e-mail address first; if that is unsuccessful, it will be sent using a fax number, if provided; if that is unsuccessful, it will be sent via US Mail.

314-621-5070 Phone:

Email: USpatents@atllp.com, clager@atllp.com

Correspondent Name: PATENT DOCKET DEPARTMENT ARMSTRONG TEASDALE LLP

Address Line 1: 7700 FORSYTH BOULEVARD

Address Line 2: **SUITE 1800** 

Address Line 4: ST. LOUIS, MISSOURI 63105

ATTORNEY DOCKET NUMBER:	28744-5409 (151087.13)
NAME OF SUBMITTER:	NICHOLAS A. KEPPEL
SIGNATURE:	/Nicholas A. Keppel/
DATE SIGNED:	09/10/2021

### **Total Attachments: 7**

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> **PATENT** REEL: 057445 FRAME: 0192

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> PATENT REEL: 057445 FRAME: 0193

### ASSIGNMENT

This Assignment is made by and among SunEdison Semiconductor Limited, a company organized and existing under the laws of Singapore ("SSL"), MEMC Japan Limited, a company organized and existing under the laws of Japan ("MEMC Japan"), and MEMC Electronic Materials, S.P.A., a company organized and existing under the laws of Italy ("MEMC EM", and collectively with SSL and MEMC Japan, the "Assignors"), and GlobalWafers Co., Ltd., a company organized and existing under the laws of Taiwan and having its registered address at No. 8. Industrial East Road, Science-Based Industrial Park, Hsinchu, Taiwan, R.O.C. (hereinafter referred to as "Assignee");

WHEREAS, on December 31, 2016, Assignors entered into certain IP Transfer Agreements with Assignee;

WHEREAS, the parties hereto desire to memorialize, *nunc pro tunc*, the assignment and ownership of all Assigned IP (defined below) for, among other things, recordal purposes with certain patent administration bodies, such as the United States Patent and Trademark Office; and

WHEREAS, Assignors acknowledge that payment in full from Assignee for all Assigned IP has heretofore been paid.

NOW, THEREFORE, for good and valuable consideration, the receipt and sufficiency of which is hereby acknowledged, Assignors have agreed to and do hereby sell, assign and transfer, and confirm the sale, assignment and transfer, unto Assignee all of their rights, title and interest throughout the world, including without limitation, the right to sue and recover for any past infringements, in and to the Listed IP, any other applications (including provisional, non-provisional, divisional, continuing, or reissue applications) based in whole or in part on any Listed IP, any corresponding patent or patent applications filed in any country based in whole or in part on, and/or claiming priority from, any Listed IP, any patents (including extensions thereof) of any country based in whole or in part on, and/or claiming priority from, any Listed IP, and all of the inventions described in the Listed IP and all of the aforementioned patents and patent applications (all of the foregoing, collectively, the "Assigned IP");

TO BE HELD AND ENJOYED by said Assignee, its successors and assigns, as fully and entirely as the Assigned IP would have been held and enjoyed by Assignors had no assignment of said interest been made.

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EACH ASSIGNOR hereby agrees that it will do, execute and deliver, or will cause to be done, executed and delivered, all such further lawful acts, transfers, assignments and conveyances, powers of attorney and assurances for the better assuring, conveying and confirming unto Assignee, all of such Assignor's rights, title and interest in and to the Assigned IP hereby transferred, assigned and conveyed, as Assignee may reasonably require.

[Signature Pages Follow]

Assignor:

SUNEDISON SEMICONDUCTOR LIMITED

By:

Name: Paul Markowitz

Title:

Director of Intellectual Property

STATE OF MUSICI

COUNTY OF At. Charles

On this \_\_\_\_\_\_\_\_, day of \_\_\_\_\_\_\_\_\_\_, 2018, before me, a Notary Public, personally appeared Paul Markowitz, an officer of SUNEDISON SEMICONDUCTOR LIMITED, known to me to be the person who executed the within Assignment, and who did state that said instrument was signed on behalf of said company, and acknowledged to me that he executed the same for the purposes therein stated.

IN TESTIMONY WHEREOF, I have hereunto set my hand and seal the date and year last above written,

Motory Dublic

My Commission Expires:

July 20, 2018

Commission and Table County

Assignor:

MEMC JAPAN LTD

Name: Paul Markowitz

Title:

Director of Intellectual Property

COUNTY OF 11. Charles

Markowitz, an officer of MEMC JAPAN LTD, known to me to be the person who executed the within Assignment, and who did state that said instrument was signed on behalf of said company, and acknowledged to me that he executed the same for the purposes therein stated.

IN TESTIMONY WHEREOF, I have hereunto set my hand and seal the date and year last above written.

My Commission Expires:

July 20, 2018

Assignor:

MEMC ELECTRONIC MATERIALS S.P.A.

By:

Name: Paul Markowitz

Title:

Director of Intellectual Property

COUNTY OF St. Charles

within Assignment, and who did state that said instrument was signed on behalf of said company, and acknowledged to me that he executed the same for the purposes therein stated.

IN TESTIMONY WHEREOF, I have hereunto set my hand and seal the date and year last above written.

My Commission Expires:

July 20, 2018

For and on behalf of GlobalWafers Co., Ltd.

Assignee:

GLOBALWAFERS CO., LTD.

Name: Paul Markowitz

Title:

Director of Intellectual Property

COUNTY OF St. Charles

On this \_\_\_\_\_\_ day of \_\_\_\_ , 2018, before me, a Notary Public, personally appeared Paul Markowitz, an officer of GLOBALWAFERS CO., LTD., known to me to be the person who executed the within Assignment, and who did state that said instrument was signed on behalf of said company, and acknowledged to me that he executed the same for the purposes therein stated.

IN TESTIMONY WHEREOF, I have hereunto set my hand and seal the date and year last above written.

My Commission Expires:

July 20, 2018

# SCHEDULE A

ппе	Country	Application Number	Filing Date	Publication Number	Publication Date	Patent Number	issue Date
PROCESS AND PLANT FOR THE PURIFICATION OF TRICHLOROSILANE AND SILICON TETRACHLORIDE	ON ON	20073126	18-Jun-2007	000000000000000000000000000000000000000	000000000000000000000000000000000000000	000000000000000000000000000000000000000	
PROCESS AND PLANT FOR THE PURIFICATION OF TRICHLOROSILANE AND SILICON TETRACHLORIDE	N N	200580039715.7	19-May-2007	CN101065324A	31-Oct-2007	ZL200580039715.7	16-Mar-2011
PROCESS AND PLANT FOR THE PURIFICATION OF TRICHLOROSILANE AND SILICON TETRACHLORIDE	Z	3611/DELNP/2007	15-May-2007	3611/DELNP/2007A	31-Aug-2007	276554	25-Oct-2016
PROCESS AND PLANT FOR THE PURIFICATION OF TRICHLOROSILANE AND SILICON TETRACHLORIDE	SG	200703413-5	19-Apr-2007			133641	29-Jul-2011
PROCESS FOR THE PURIFICATION OF TRICHLOROSILANE AND SILICON TETRACHLORIDE	sn	11/719688	21-Aug-2007	2008-0314728	25-Dec-2008	7879198	1-Feb-2011
PROCESS AND PLANT FOR THE PURIFICATION OF TRICHLOROSILANE AND SILICON TETRACHLORIDE	SG	200907702-5	19-Nov-2009	0158071	29-Jan-2010	158071	28-Jun-2013
PROCESS FLOW FOR MANUFACTURING SEMICONDUCTOR ON INSULATOR STRUCTURES IN PARALLEL	SN	15/435428	17-Feb-2017	2017-0243781	24-Aug-2017	9831115	28-Nov-2017
SEMICONDUCTOR ON INSULATOR STRUCTURE COMPRISING A BURIED HIGH RESISTIVITY LAYER	WO	PCT/US2017/017756	14-Feb-2017	WO 2017/142849	24-Aug-2017		
HIGH RESISTIVITY SILICON-ON- INSULATOR SUBSTRATE COMPRISING A CHARGE TRAPPING LAYER FORMED ON A SUBSTRATE WITH A ROUGH SURFACE	WO	PCT/US2017/015813	31-Jan-2017	WO 2017/142704	24-Aug-2017		
HIGH RESISTIVITY SINGLE CRYSTAL SILICON INGOT AND WAFER HAVING IMPROVED MECHANICAL STRENGTH	O/A	PCT/US2017/036061	6-Jun-2017	WO 2017/214084	14-Dec-2017		
HIGH RESISTIVITY SINGLE CRYSTAL SILICON INGOT AND WAFER HAVING IMPROVED MECHANICAL STRENGTH	ΛΛ	106119035	8-Jun-2017	201809377	16-Mar-2018		
HIGH RESISTIVITY SILICON-ON- INSULATOR SUBSTRATE HAVING ENHANCED CHARGE TRAPPING EFFICIENCY	ΤW	106136283	23-Oct-2017				
HIGH RESISTIVITY SILICON-ON- INSULATOR SUBSTRATE HAVING ENHANCED CHARGE TRAPPING EFFICIENCY	SN	15/727723	9-Oct-2017	2018-0114720	26-Apr-2018		
HIGH RESISTIVITY SILICON-ON- INSULATOR SUBSTRATE HAVING ENHANCED CHARGE TRAPPING EFFICIENCY	WO	PCT/US2017/055722	9-Oct-2017	WO 2018/080772	3-May-2018		
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